# **CPC** COOPERATIVE PATENT CLASSIFICATION

## H ELECTRICITY

(NOTE omitted)

## H01 ELECTRIC ELEMENTS (NOTES omitted)

### H01C RESISTORS

## NOTES

- 1. In this subclass, the term "adjustable" means mechanically adjustable.
- 2. Variable resistors, the value of which is changed non-mechanically, e.g. by voltage or temperature, are classified in group H01C 7/00.

#### WARNING

In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

#### 1/00 Details

1/01	Mounting; Supporting
1/012	• the base extending along and imparting rigidity or reinforcement to the resistive element
	(H01C 1/016 takes precedence; the resistive
	element being formed in two or more coils or
	loops as a spiral, helical or toroidal winding
	<u>H01C 3/18, H01C 3/20;</u> the resistive element
	being formed as one or more layers or coatings on a base <u>H01C 7/00</u> )
1/014	the resistor being suspended between and
	being supported by two supporting sections
	(H01C 1/016 takes precedence)
1/016	• • with compensation for resistor expansion or contraction
1/02	. Housing; Enclosing; Embedding; Filling the
	housing or enclosure
1/022	• • the housing or enclosure being openable or
	separable from the resistive element
1/024	• the housing or enclosure being hermetically
	sealed ( <u>H01C 1/028</u> , <u>H01C 1/032</u> , <u>H01C 1/034</u>
	take precedence)
1/026	• • • with gaseous or vacuum spacing between the
1/020	resistive element and the housing or casing
1/028	• the resistive element being embedded in
1/03	insulation with outer enclosing sheath
	• • • with powdered insulation
1/032	• plural layers surrounding the resistive element (H01C 1/028 takes precedence)
1/034	• the housing or enclosure being formed as coating
1,001	or mould without outer sheath (H01C $1/032$ takes
	precedence)
1/036	on wound resistive element
1/04	• Arrangements of distinguishing marks, e.g. colour
	coding
1/06	• Electrostatic or electromagnetic shielding
	arrangements
1/08	Cooling, heating or ventilating arrangements
1/082	• • using forced fluid flow
1/084	• • using self-cooling, e.g. fins, heat sinks
1/12	Arrangements of current collectors
1/125	• • of fluid contacts

1/14	• Terminals or tapping points {or electrodes} specially adapted for resistors (in general <u>H01R</u> ); Arrangements of terminals or tapping points {or electrodes} on resistors
1/1406	• {Terminals or electrodes formed on resistive elements having positive temperature coefficient}
1/1413	• • {Terminals or electrodes formed on resistive elements having negative temperature coefficient}
1/142	• the terminals or tapping points being coated on the resistive element
1/144	• the terminals or tapping points being welded or soldered
1/146	the resistive element surrounding the terminal
1/148	• the terminals embracing or surrounding the resistive element ( <u>H01C 1/142</u> takes precedence)
1/16	. Resistor networks not otherwise provided for
3/00	Non-adjustable metal resistors made of wire or
	ribbon, e.g. coiled, woven or formed as grids
3/005	• {Metallic glasses therefor}
3/02	• arranged or constructed for reducing self-induction,
	capacitance or variation with frequency
3/04	<ul> <li>Iron-filament ballast resistors; Other resistors having variable temperature coefficient</li> </ul>
3/06	• Flexible or folding resistors, whereby such a resistor can be looped or collapsed upon itself
3/08	• Dimension or characteristic of resistive element changing gradually or in discrete steps from one terminal to another
3/10	<ul> <li>the resistive element having zig-zag or sinusoidal configuration</li> </ul>
3/12	• • lying in one plane
3/14	• the resistive element being formed in two or more
	coils or loops continuously wound as a spiral, helical or toroidal winding ( <u>H01C 3/02</u> - <u>H01C 3/12</u> take precedence)
3/16	• including two or more distinct wound elements or
5/10	two or more winding patterns
3/18	<ul> <li>wound on a flat or ribbon base (<u>H01C 3/16</u> takes precedence)</li> </ul>

3/20	• • wound on cylindrical or prismatic base ( <u>H01C 3/16</u> takes precedence)
7/00	Non-adjustable resistors formed as one or more layers or coatings; Non-adjustable resistors made from powdered conducting material or
	powdered semi-conducting material with or without insulating material (consisting of loose
	powdered or granular material <u>H01C 8/00</u> ; resistors
	having potential barriers, e.g. field-effect resistors,
	H01L 29/00; semiconductor devices sensitive
	to electromagnetic or corpuscular radiation, e.g.
	photoresistors, <u>H01L 31/00</u> ; magnetic field controlled
	resistors <u>H10N 50/10</u> ; bulk negative resistance effect devices <u>H10N 80/00</u> )
7/001	• {Mass resistors}
7/003	• {Thick film resistors}
7/005	• {Polymer thick films}
7/006	• {Thin film resistors}
7/008	• {Thermistors ( <u>H01C 7/02</u> - <u>H01C 7/06</u> take
	precedence)}
7/02	<ul> <li>having positive temperature coefficient {(ceramics C04B)}</li> </ul>
7/021	• • {formed as one or more layers or coatings}
7/022	• • {mainly consisting of non-metallic substances
7/022	( <u>H01C 7/021</u> takes precedence)}
7/023	<ul> <li>. {containing oxides or oxidic compounds, e.g. ferrites}</li> </ul>
7/025	• • • • {Perovskites, e.g. titanates}
7/026	•••• {Vanadium oxides or oxidic compounds, e.g. VOx}
7/027	• • {consisting of conducting or semi-conducting
	material dispersed in a non-conductive organic
7/028	<ul><li>material }</li><li> {consisting of organic substances }</li></ul>
7/028	<ul> <li>A consisting of organic substances?</li> <li>having negative temperature coefficient</li> </ul>
//01	{(thermometers using resistive elements
	<u>G01K 7/16</u> )}
	NOTE
	{In groups $\underline{H01C 7/043}$ - $\underline{H01C 7/049}$ , the
	last place priority rule is applied, i.e. at each hierarchical level, in the absence of an indication
	to the contrary, classification is made in the last
	appropriate place.}
7/041	• {formed as one or more layers or coatings}
7/041	<ul> <li>{formed as one of more layers of coarnigs}</li> <li>{mainly consisting of inorganic non-metallic</li> </ul>
11042	substances ( <u>H01C 7/041</u> takes precedence)}
7/043	• • • {Oxides or oxidic compounds}
7/044	{Zinc or cadmium oxide}
7/045	• • • • {Perovskites, e.g. titanates}
7/046	{Iron oxides or ferrites}
7/047	•••• {Vanadium oxides or oxidic compounds, e.g. VOx}
7/048	• • • {Carbon or carbides}
7/049	• {mainly consisting of organic or organo-metal substances ( <u>H01C 7/041</u> takes precedence)}
7/06	<ul> <li>including means to minimise changes in resistance</li> </ul>
,, 00	with changes in temperature
7/10	• voltage responsive, i.e. varistors
7/1006	• • {Thick film varistors}
7/1013	• • {Thin film varistors}
7/102	• Varistor boundary, e.g. surface layers ( <u>H01C 7/12</u>
	takes precedence)

7/105	• Varistor cores (H01C 7/12 takes precedence)
7/108	Metal oxide
7/112	ZnO type
7/115	Titanium dioxide- or titanate type
7/118	Carbide, e.g. SiC type
7/12	• Overvoltage protection resistors {(series resistors structurally associated with spark gaps H01T 1/16)}
7/123	• • { Arrangements for improving potential distribution }
7/126	• • • {Means for protecting against excessive pressure or for disconnecting in case of failure}
7/13	current responsive
	<u>NOTE</u>
	Groups $\underline{H01C 7/02}$ - $\underline{H01C 7/13}$ take precedence over groups $\underline{H01C 7/18}$ - $\underline{H01C 7/22}$ .
7/18	<ul> <li>comprising a plurality of layers stacked between terminals</li> </ul>
7/20	• the resistive layer or coating being tapered
7/22	• Elongated resistive element being bent or curved, e.g. sinusoidal, helical
8/00	Non-adjustable resistors consisting of loose powdered or granular conducting, or powdered or granular semi-conducting material
8/02	• Coherers or like imperfect resistors for detecting electromagnetic waves
8/04	Overvoltage protection resistors; Arresters
10/00	Adjustable resistors
10/005	• {Surface mountable, e.g. chip trimmer potentiometer}
10/02	. Liquid resistors
10/025	<ul> <li>{Electrochemical variable resistors (trimming resistors by electrolytic treatment <u>H01C 17/2412</u>, <u>H01C 17/262</u>)}</li> </ul>
10/04	<ul> <li>with specified mathematical relationship between movement of resistor actuating means and value of resistance, other than direct proportional relationship</li> </ul>
10/06	<ul> <li>adjustable by short-circuiting different amounts of the resistive element</li> </ul>
10/08	• • with intervening conducting structure between the resistive element and the short-circuiting means, e.g. taps
10/10	• adjustable by mechanical pressure or force
10/103	<ul> <li>{by using means responding to magnetic or electric fields, e.g. by addition of magnetisable or piezoelectric particles to the resistive material, or by an electromagnetic actuator}</li> </ul>
10/106	• {on resistive material dispersed in an elastic material ( <u>H01C 10/103</u> and <u>H01C 10/12</u> take precedence; for electric switches <u>H01H 1/029</u> )}
10/12	• by changing surface pressure between resistive masses or resistive and conductive masses, e.g. pile type
10/14	• adjustable by auxiliary driving means
10/16	• including plural resistive elements
10/18	including coarse and fine resistive elements
10/20	• Contact structure or movable resistive elements being ganged

10/22	• resistive element dimensions changing gradually
	in one direction, e.g. tapered resistive element
	(H01C 10/04 takes precedence)
10/23	<ul> <li>resistive element dimensions changing in a series of discrete, progressive steps</li> </ul>
10/24	• the contact moving along turns of a helical resistive element, or vica versa
10/26	<ul> <li>resistive element moving (<u>H01C 10/16</u>, <u>H01C 10/24</u></li> </ul>
10/20	take precedence)
	NOTE
	Groups H01C 10/02 - H01C 10/26
	take precedence over groups
	<u>H01C 10/28</u> - <u>H01C 10/50</u> .
10/28	• the contact rocking or rolling along resistive
10/20	element or taps
10/30	• the contact sliding along resistive element
10/301	• • {consisting of a wire wound resistor}
10/303	• • { the resistor being coated, e.g. lubricated,
	conductive plastic coated, i.e. hybrid
	potentiometer}
10/305	• • {consisting of a thick film}
10/306	• • • {Polymer thick film, i.e. PTF}
10/308	• • {consisting of a thin film}
10/32	• • the contact moving in an arcuate path
10/34	the contact or the associated conducting
	structure riding on collector formed as a ring or portion thereof
10/345	• • • { the collector and resistive track being situated in 2 parallel planes }
10/36	• • structurally combined with switching arrangements
10/363	•••• {by axial movement of the spindle, e.g.
	pull-push switch (H01C 10/366 takes
	precedence)}
10/366	• • • • {using an electromagnetic actuator}
10/38	• • the contact moving along a straight path
10/40	screw operated
10/42	•••• the contact bridging and sliding along resistive element and parallel conducting bar
	or collector
10/44	• • • the contact bridging and sliding along resistive element and parallel conducting bar or collector (H01C 10/42 takes precedence)
10/46	• Arrangements of fixed resistors with intervening
10/40	connectors, e.g. taps ( <u>H01C 10/28</u> , <u>H01C 10/30</u> take precedence)
10/48	• including contact movable in an arcuate path
10/50	<ul> <li>structurally combined with switching arrangements</li> </ul>
10/00	( <u>H01C 10/36</u> takes precedence)
11/00	Non-adjustable liquid resistors
13/00	Resistors not provided for elsewhere
13/02	• Structural combinations of resistors (impedance
	networks <u>per se H03H</u> )
17/00	Apparatus or processes specially adapted for
1//00	manufacturing resistors (providing fillings
	for housings or enclosures <u>H01C 1/02</u> ; reducing
	insulation surrounding a resistor to powder
	H01C 1/03; manufacture of thermally variable
	resistors <u>H01C 7/02</u> , <u>H01C 7/04</u> )

17/003	
	• {using lithography, e.g. photolithography
	(lithographic compositions and processing in
	general <u>G03F</u> )}
17/006	• {adapted for manufacturing resistor chips}
17/02	adapted for manufacturing resistors with envelope
	or housing
17/04	<ul> <li>adapted for winding the resistive element</li> </ul>
17/06	adapted for coating resistive material on a base
17/065	• • by thick film techniques, e.g. serigraphy
17/06506	• • • {Precursor compositions therefor, e.g. pastes,
	inks, glass frits}
17/06513	• • • {characterised by the resistive component}
17/0652	• • • • {containing carbon or carbides}
17/06526	• • • • {composed of metals}
17/06533	• • • • {composed of oxides}
17/0654	•••• {Oxides of the platinum group}
17/06546	••••• {Oxides of zinc or cadmium}
17/06553	{composed of a combination of metals and
	oxides}
17/0656	••••• {composed of silicides ( <u>H01C 17/0652</u>
	takes precedence)}
17/06566	••••• {composed of borides ( <u>H01C 17/0652</u>
	takes precedence)}
17/06573	• • • {characterised by the permanent binder}
17/0658	{composed of inorganic material}
17/06586	• • • • {composed of organic material}
17/06593	• • • {characterised by the temporary binder}
17/07	• • by resistor foil bonding, e.g. cladding
17/075	• • by thin film techniques {( <u>H01C 17/20</u> takes
	precedence)}
17/08	• • • by vapour deposition
17/10	• • • by flame spraying
17/12	• • • by sputtering
17/14	• • • by chemical deposition
17/16	using electric current
17/18	• • • • without using electric current
17/18 17/20	• • by pyrolytic processes
	<ul><li>by pyrolytic processes</li><li>adapted for trimming</li></ul>
17/20	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of</li> </ul>
17/20 17/22 17/23	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> </ul>
17/20 17/22	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting</li> </ul>
17/20 17/22 17/23	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature</li> </ul>
17/20 17/22 17/23 17/232	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> </ul>
17/20 17/22 17/23	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for</li> </ul>
17/20 17/22 17/23 17/232 17/235	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> </ul>
17/20 17/22 17/23 17/232	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material</li> </ul>
17/20 17/22 17/23 17/232 17/235	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> </ul>
17/20 17/22 17/23 17/232 17/232	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by electrolytic treatment, e.g. electroplating</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408 17/2412	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by electrolytic treatment, e.g. electroplating (for anodic oxydation H01C 17/262)}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by chemical etching}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408 17/2412 17/2416	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by chemical etching}</li> <li>{by chemical etching}</li> <li>by laser {(trimming by laser in general</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408 17/2412 17/2416	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by chemical etching}</li> <li>{by chemical etching}</li> <li>by laser {(trimming by laser in general B23K 26/351)}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2404 17/2408 17/2412 17/2416 17/2416 17/242	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by electrolytic treatment, e.g. electroplating (for anodic oxydation H01C 17/262)}</li> <li>{by chargel technig}</li> <li>by laser {(trimming by laser in general B23K 26/351)}</li> <li>by mechanical means, e.g. sand blasting,</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2404 17/2408 17/2412 17/2416 17/2416 17/242	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by chemical etching}</li> <li>{by chemical etching}</li> <li>by laser {(trimming by laser in general B23K 26/351)}</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408 17/2412 17/2416 17/2416 17/242 17/245	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by pulsed voltage erosion, e.g. spark erosion}</li> <li>{by chemical etching}</li> <li>by laser {(trimming by laser in general B23K 26/351)}</li> <li>by mechanical means, e.g. sand blasting, cutting, ultrasonic treatment</li> <li>by converting resistive material</li> </ul>
17/20 17/22 17/23 17/232 17/235 17/24 17/2404 17/2408 17/2412 17/2416 17/2416 17/242 17/245 17/245	<ul> <li>by pyrolytic processes</li> <li>adapted for trimming</li> <li>by opening or closing resistor geometric tracks of predetermined resistive values, {e.g. snapistors}</li> <li>Adjusting the temperature coefficient; Adjusting value of resistance by adjusting temperature coefficient of resistance</li> <li>Initial adjustment of potentiometer parts for calibration</li> <li>by removing or adding resistive material (H01C 17/23, H01C 17/232, H01C 17/235 take precedence)</li> <li>{by charged particle impact, e.g. by electron or ion beam milling, sputtering, plasma etching}</li> <li>{by electrolytic treatment, e.g. electroplating (for anodic oxydation H01C 17/262)}</li> <li>{by chemical etching}</li> <li>by laser {(trimming by laser in general B23K 26/351)}</li> <li>by mechanical means, e.g. sand blasting, cutting, ultrasonic treatment</li> <li>by converting resistive material</li> </ul>

17/265	• • {by chemical or thermal treatment, e.g.
	oxydation, reduction, annealing (etching
	<u>H01C 17/2416</u> )}
17/267	• • • {by passage of voltage pulses or electric
	current}
17/28	• adapted for applying terminals
17/281	• • {by thick film techniques}
17/283	• • • {Precursor compositions therefor, e.g. pastes,
	inks, glass frits}
17/285	{applied to zinc or cadmium oxide resistors}
17/286	• • • • {applied to $TiO_2$ or titanate resistors}
17/288	• • {by thin film techniques}
17/30	• adapted for baking